

APR 5 2003



THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of

)

Shunpei YAMAZAKI et al.

) Group Art Unit: 2811

Serial No. 09/535,015

) Examiner: S. Crane

Filed: March 24, 2000

)

For: METHOD OF MANUFACTURING  
A SEMICONDUCTOR DEVICE

)

**CERTIFICATE OF MAILING**

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Adele M Stamper  
Adele M. Stamper

**SUPPLEMENTAL AMENDMENT**

Honorable Commissioner for Patents

Washington, D.C. 20231

Sir:

Further in response to the Office Action dated October 23, 2002, and the  
Amendment filed February 24, 2003, please amend the above-identified application as  
follows:

**IN THE SPECIFICATION:**

Please amend the specification as follows:

Please replace the paragraph bridging page 4 and 5 with the following:

According to the present invention disclosed in the present specification, chlorine is  
also contained in the atmosphere in order to promote the effect of gettering the metal. The  
effect of eliminating the metal element from the silicon film may be enhanced by forming a  
compound of the metal element, fluorine and chlorine at the time of gettering by  
introducing chlorine.

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2811  
#16 D  
Suppl. Amendment  
J. Robinson  
5/9/03